

*B-1*  
*Contd*

a second diffusion region formed in the layer adjacent to and spaced apart from the first diffusion region;

a channel region formed at a boundary between the first and second diffusion regions, wherein said channel region is bounded by first and second diffusion edges of the first diffusion region; and

at least one island formed at least partially in the first diffusion region, the at least one island being positioned non-symmetrically about a plane perpendicular to a top surface of the semiconductor layer and perpendicular to the boundary, wherein said plane bisects the channel region.

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101. (Amended) The ESD protection device of claim 1, wherein  
said at least one island having a first island edge near said first diffusion edge  
and a second island edge near said second diffusion edge;

a first gap of at least zero spacing between the first diffusion edge and a first nearest island edge;

a second gap of at least zero spacing between the second diffusion edge and a second nearest island edge; and said first gap being larger than the second gap.

*B-2*

102. (Amended) An electrostatic discharge (ESD) protection device, comprising:  
a semiconductor layer;  
a first diffusion region formed in the layer;  
a second and a third diffusion region formed in the layer each adjacent to and spaced apart from the first diffusion region;